

# ***ELPIDA***



®

## **FORMFACTOR**

The MicroSpring® Company

**Cost-Effective Fully Tested Die with  
High-Frequency and High-Throughput  
Wafer-Test Solution**

Masahide Ozawa Elpida Memory, Inc.  
Nobuhiro Kawamata FormFactor Inc., Asia

**Southwest Test Workshop 2004**

# Presentation Outline

- Mobile RAM introduction
- Mobile RAM wafer-level-final-sort tests objectives and goals
- High performance probing technology solution
- New probing technology internal qualification
- Customer qualification
- Follow on work
- Summary and conclusion

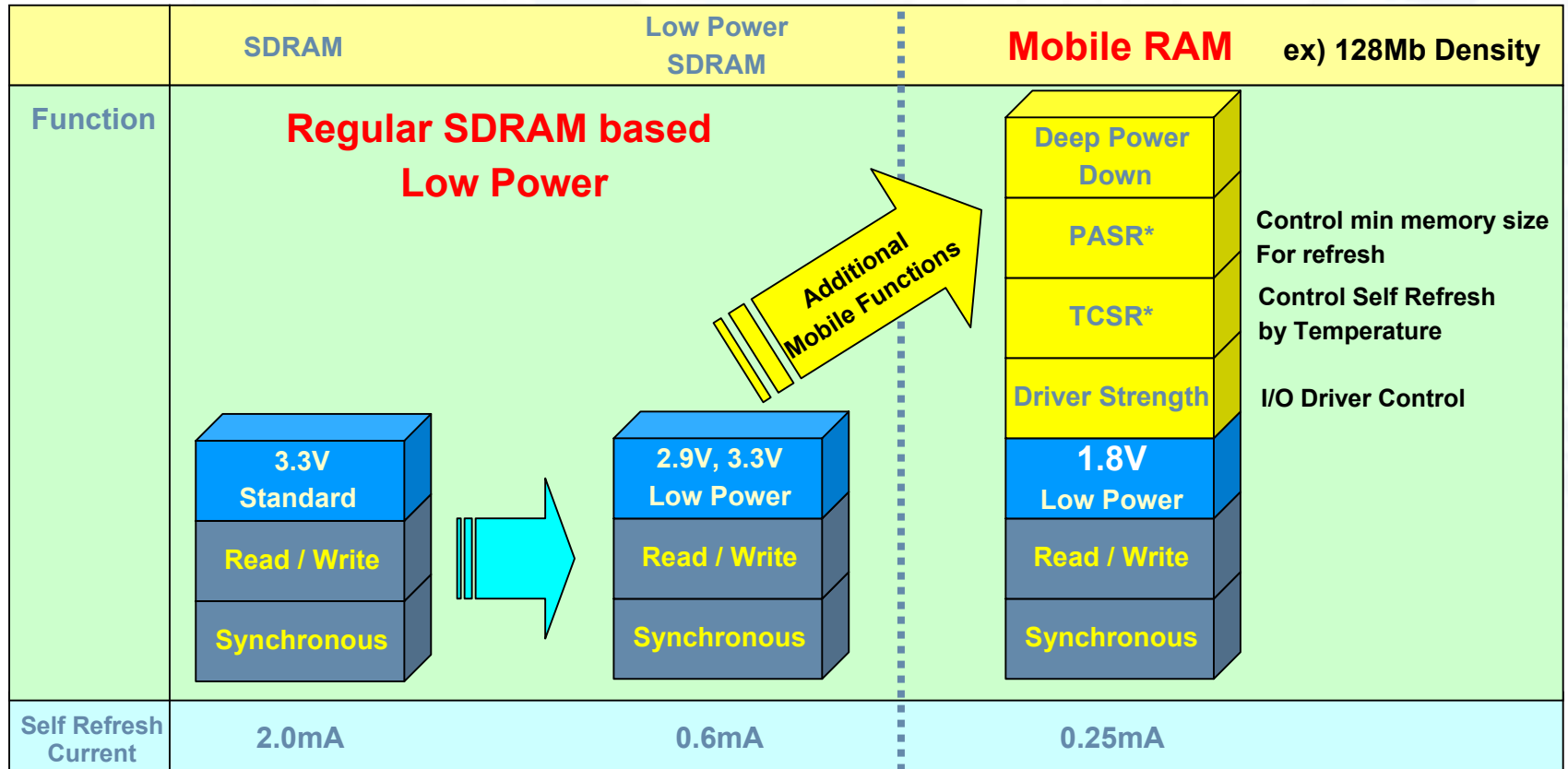
# Elpida DRAM Plant

300mm Fabrication in Japan



# Mobile RAM Introduction

## Lowest IDD6, Low Voltage (1.8V), and JEDEC Mobile Functions

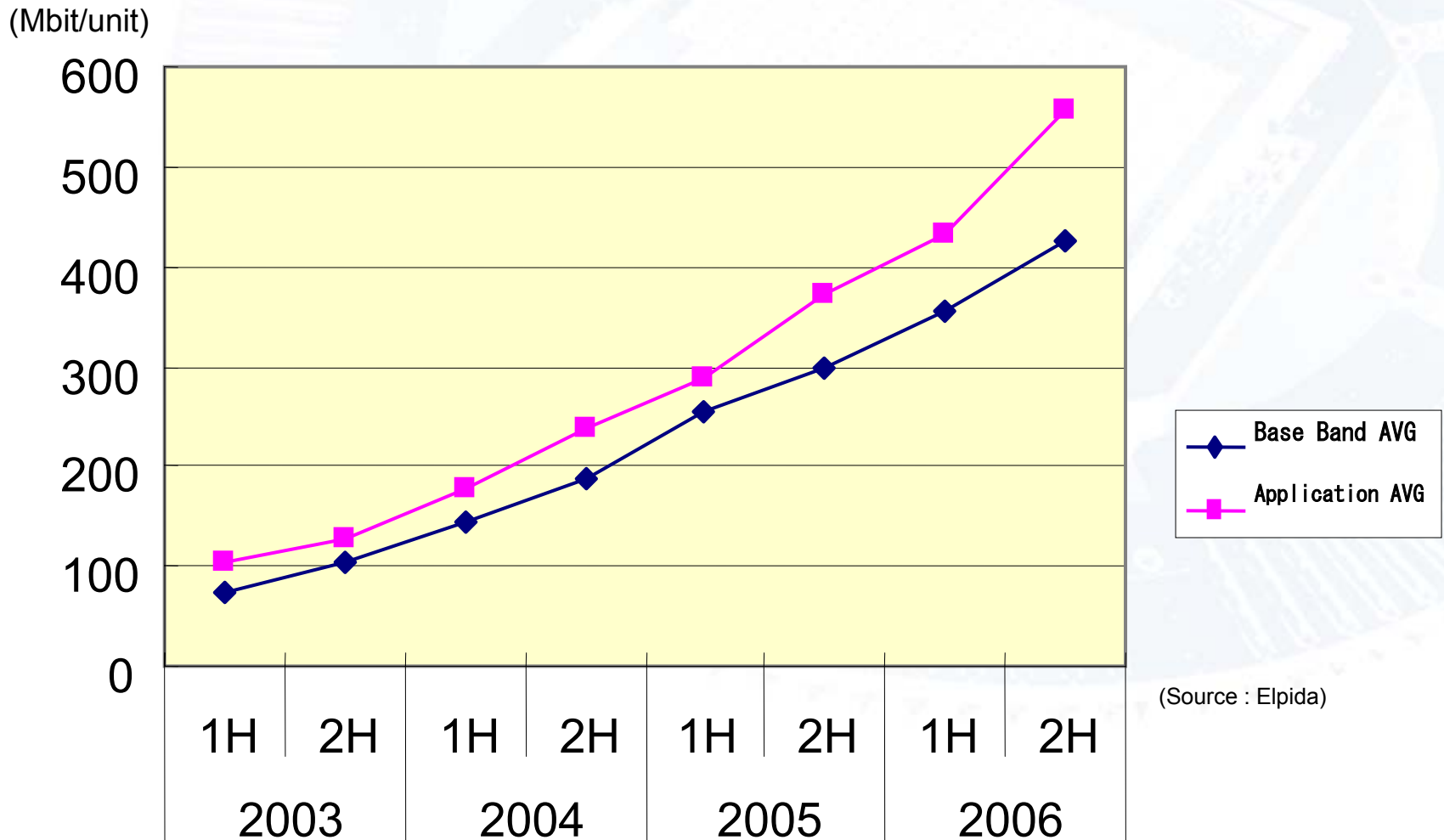


\* Low Power Mode

PASR: Partial Array Self Refresh

TCSR: Temperature Compensated Self Refresh

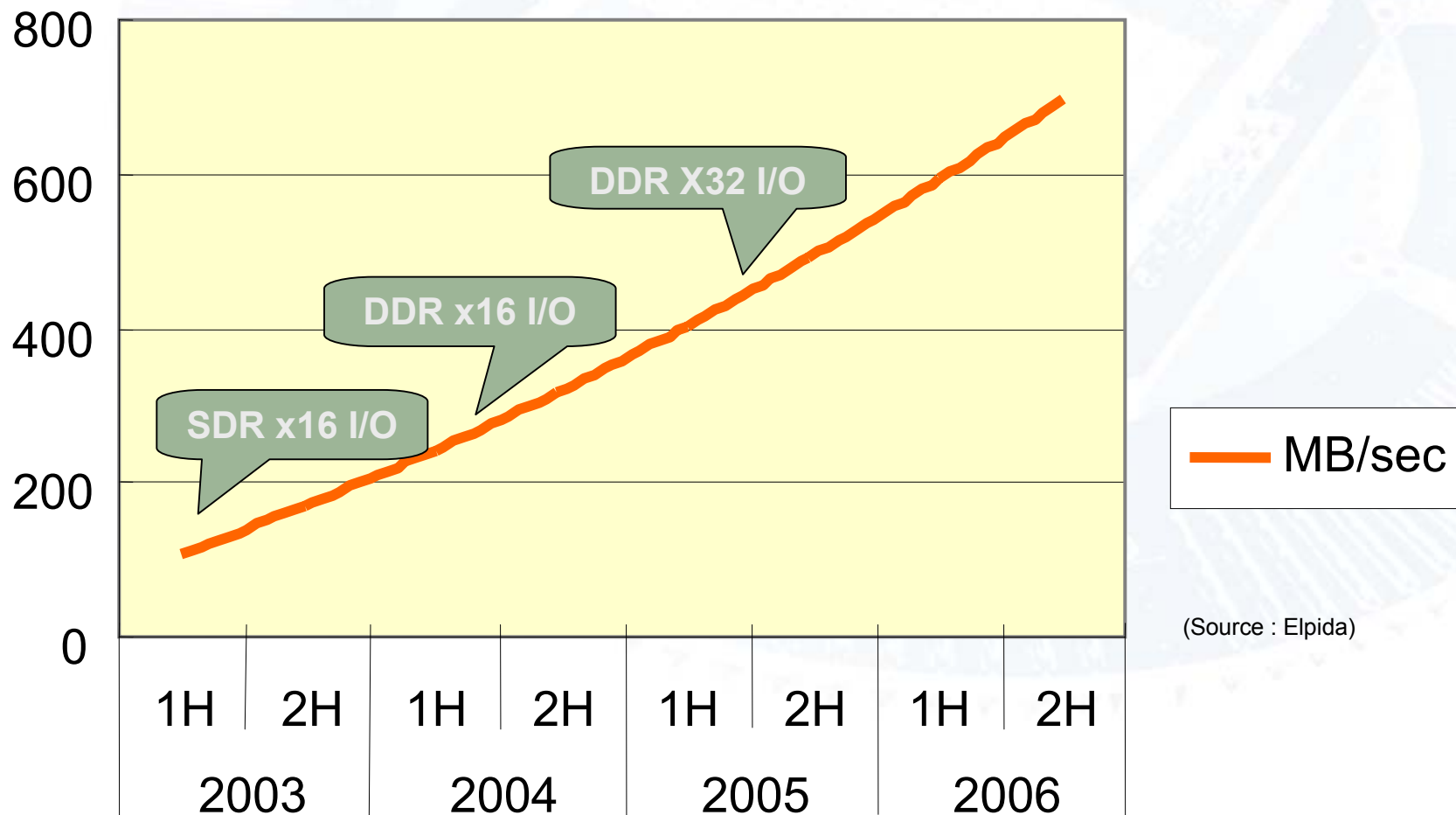
# Required Density in Cellular Phone



Application memory is higher than Baseband memory.

# Bandwidth (Speed) for Cellular Phone

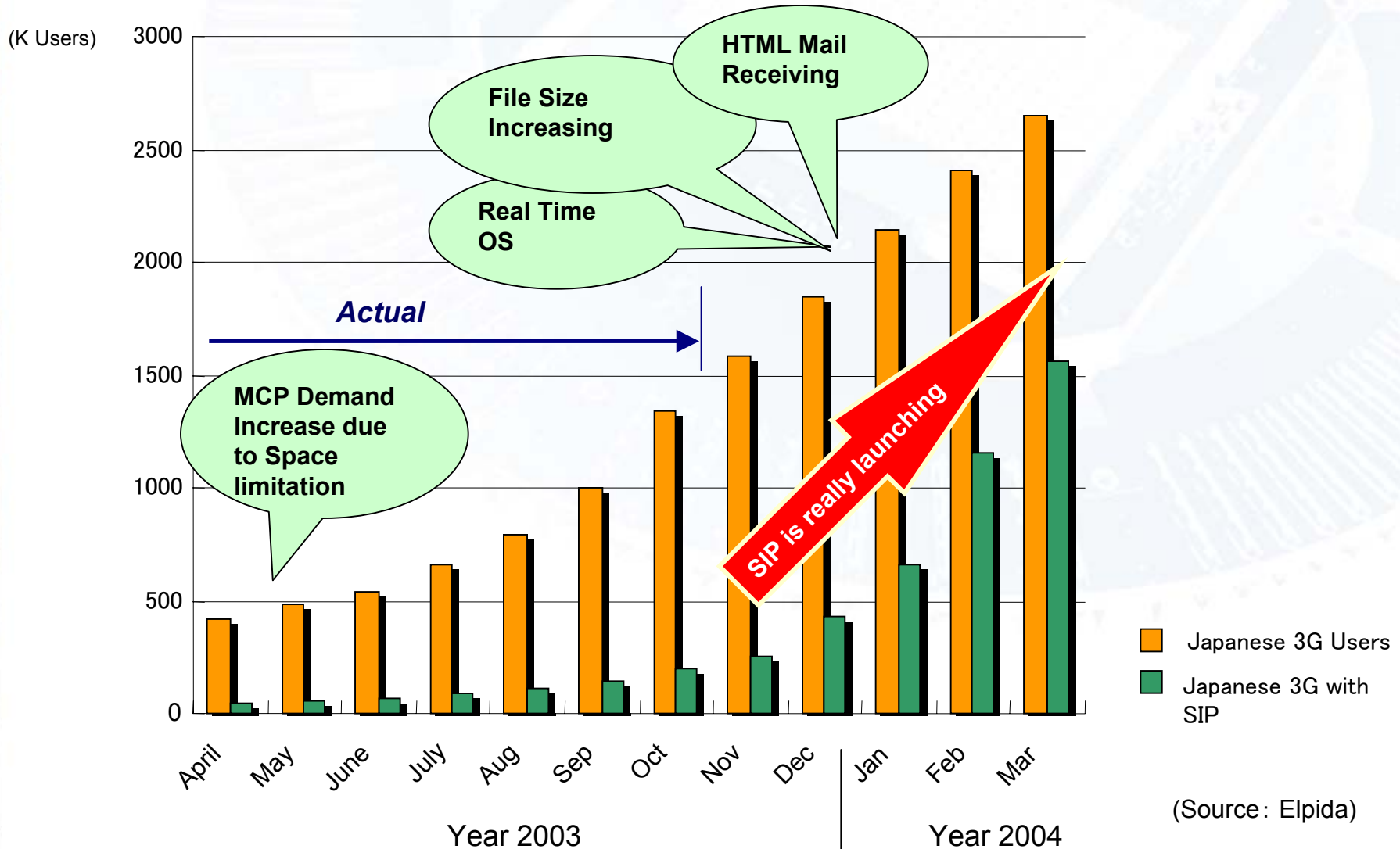
(MByte/sec)



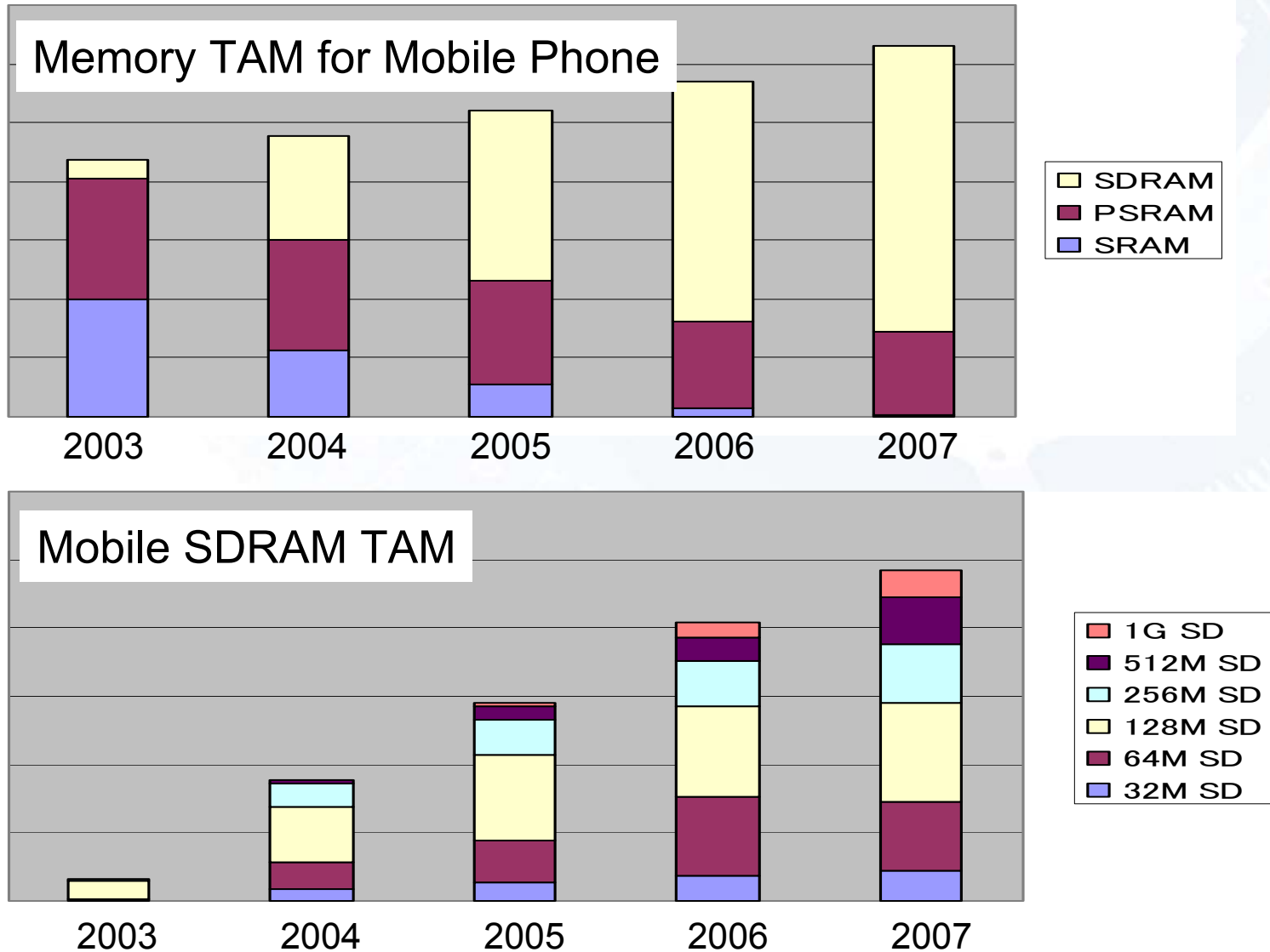
(Source : Elpida)

Due to advanced application, required bandwidth is rapidly growing.

# Japanese 3G Market Penetration Plan and SIP demand projection



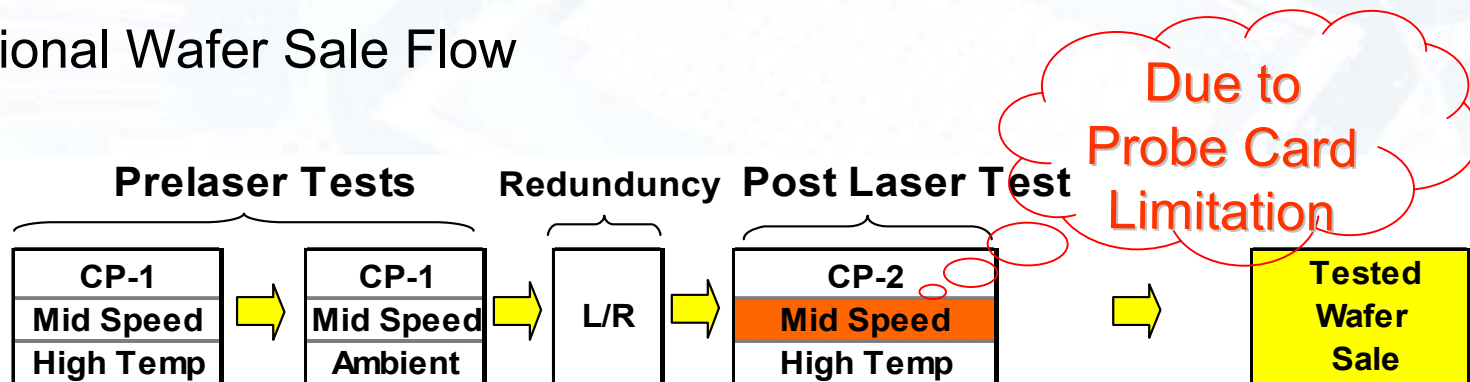
# Mobile Memory TAM Trend



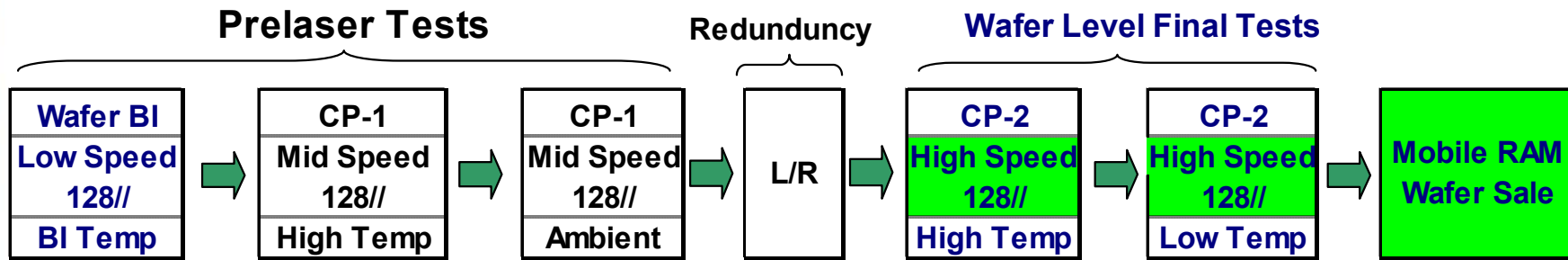


# Advanced Mobile RAM KGD Flow

- Conventional Wafer Sale Flow



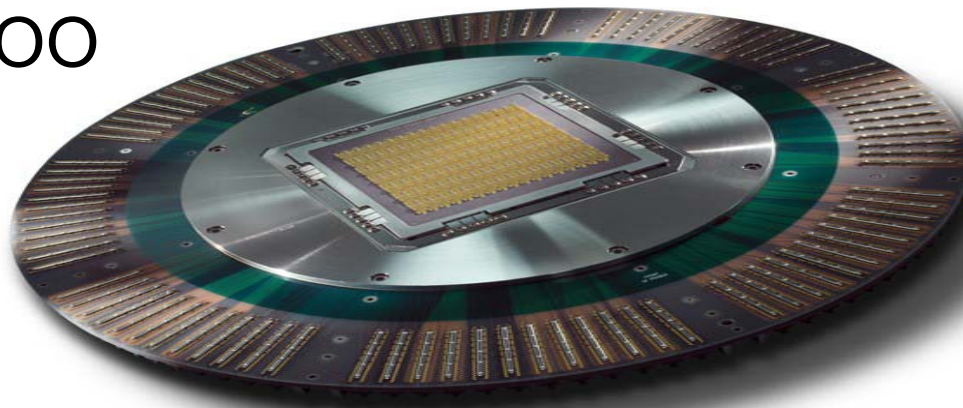
- Elpida Mobile RAM Wafer Sale Flow (Under Evaluation)



- Wafer Level BI Test
- High Speed and High Throughput Wafer Level Final Tests
- High, Ambient, Cold Test Temperature Tests

# Wafer-Level Final-Sort-at-Probe Objectives

- On-spec Mobile RAM testing
  - Low-voltage
  - High-frequency
  - Wide temperature
- Low TCOO



## High Performance Probing Solution

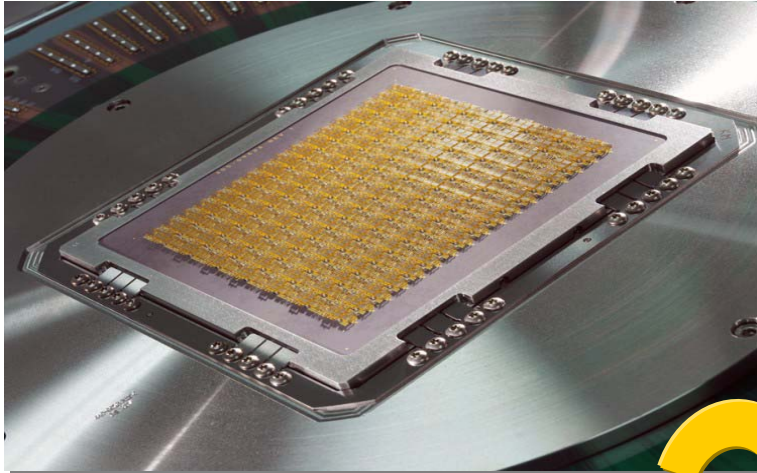
High performance probing solution enables “Value-Added Mobile RAM Wafer-Sale Business”

# High Performance Probing Solution

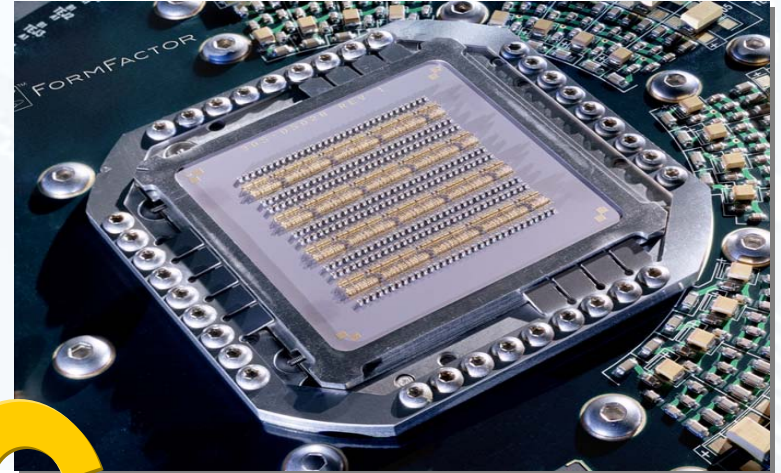
FFI S200™ probing technology

TRE™ probing technology

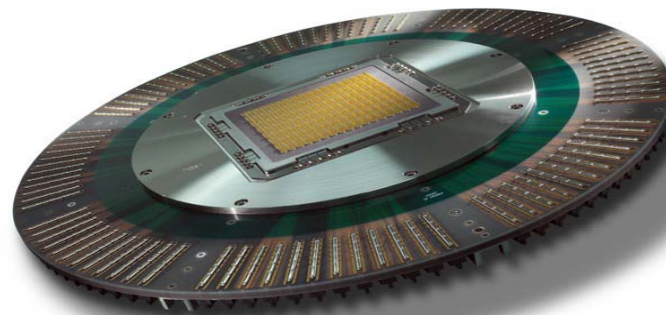
HFTAP™ probing technology



128 Multi DUT testing, 66MHz



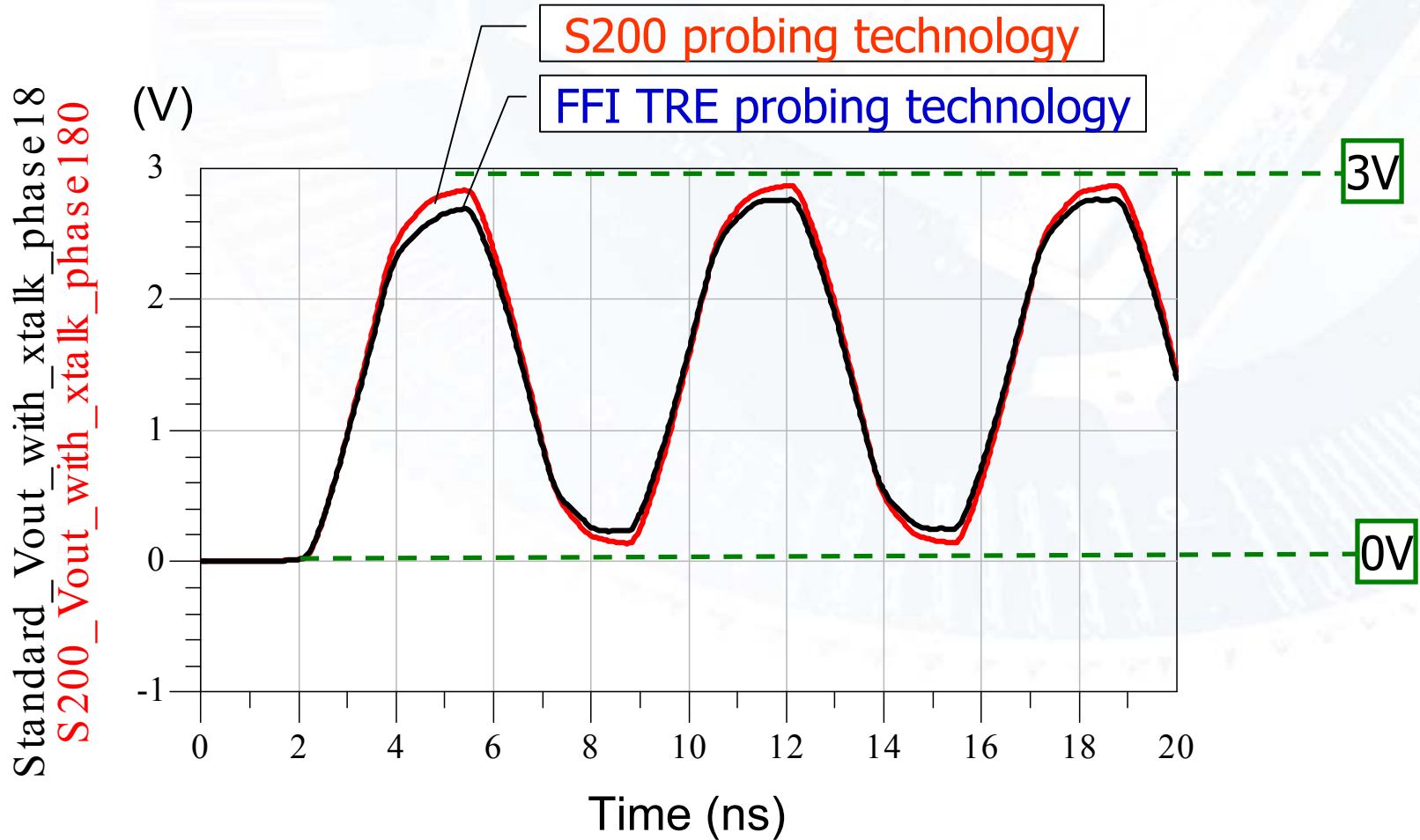
500MHz, High signal integrity



200MHz High signal integrity 128 Multi DUT

# FFI Internal Qualification

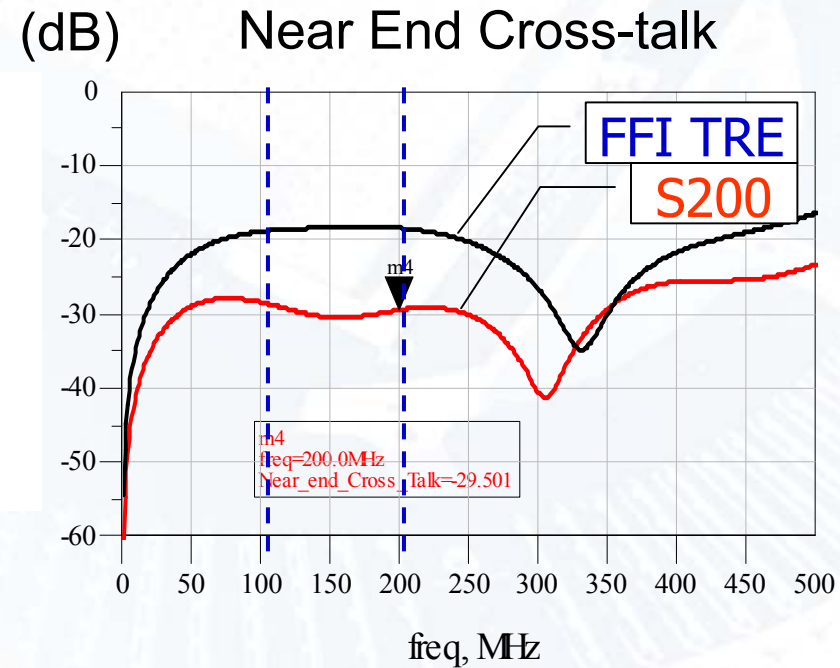
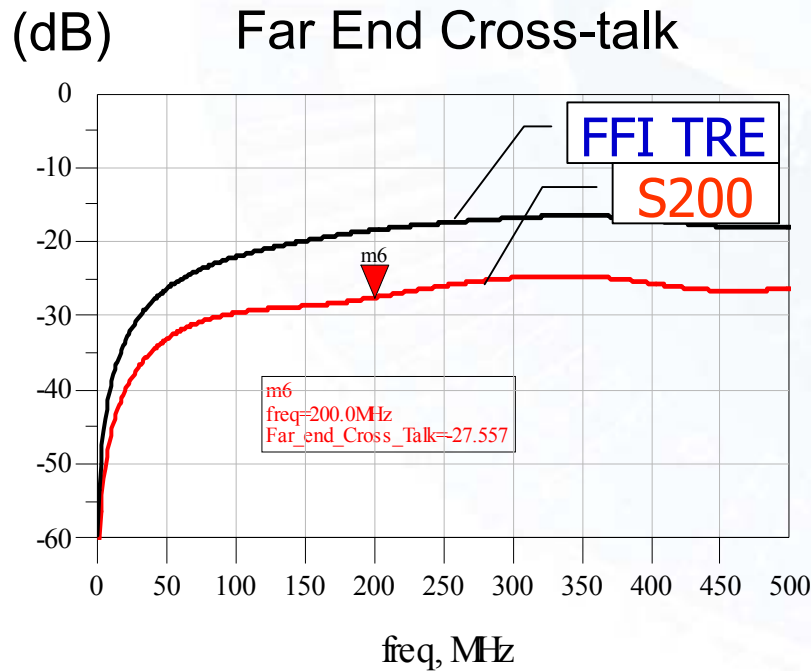
Signal Integrity: Cross-talk simulation\*



\*180° out-of-phase cross-talk effects super-imposed

# FFI Internal Qualification

## Signal Integrity: cross-talk simulation



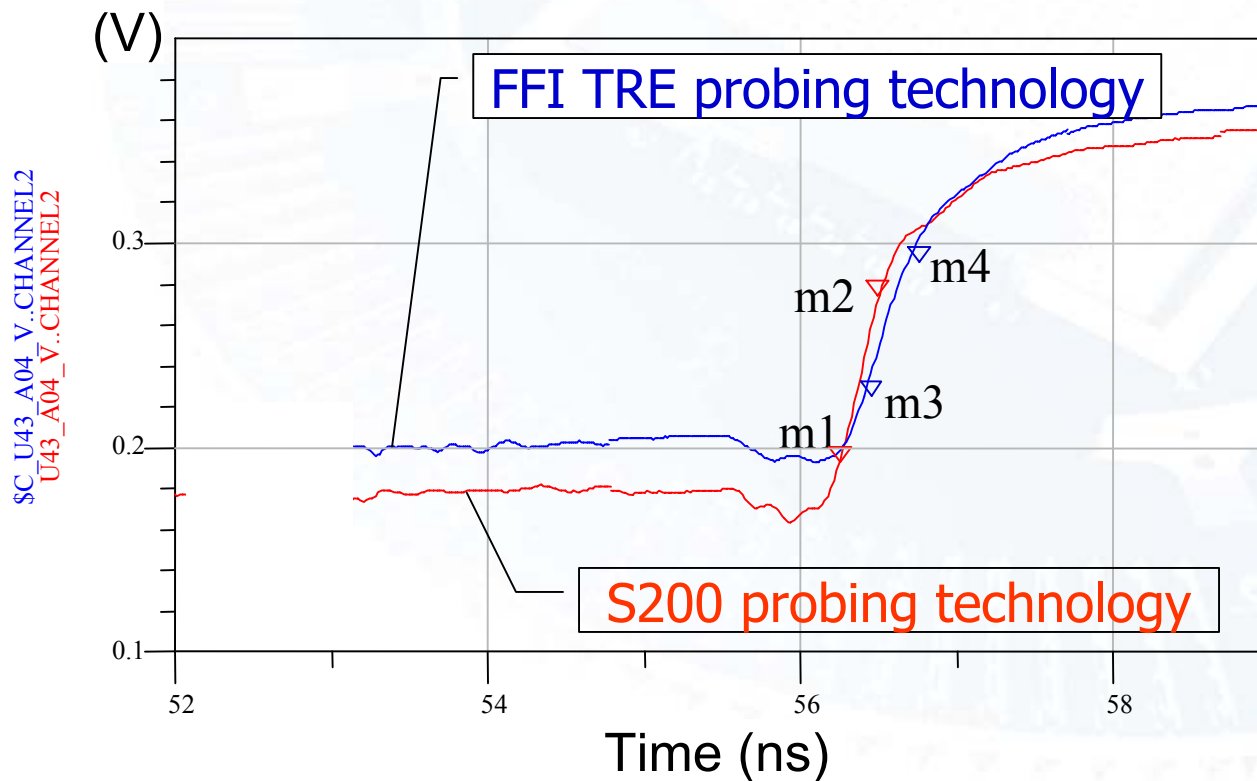
$$NEXT(dB) = 20 \log_{10} \left( \frac{V1}{V2} \right)$$

*V1: Measured Power in volts*  
*V2: Reference Power in volts*

$$-20dB = 20 \log_{10} \left( \frac{0.1}{1} \right) \therefore 10\% , \quad -30dB = 20 \log_{10} \left( \frac{0.032}{1} \right) \therefore 3.2\%$$

# FFI Internal Qualification

## Signal Integrity: Tr/Tf Measurement



FFI TRE Probing Technology	S200 Probing Technology
$t_{m3-m4} = 0.45\text{ns}$	$t_{m1-m2} = 0.35\text{ns}$

# S200 Internal Qualification Results

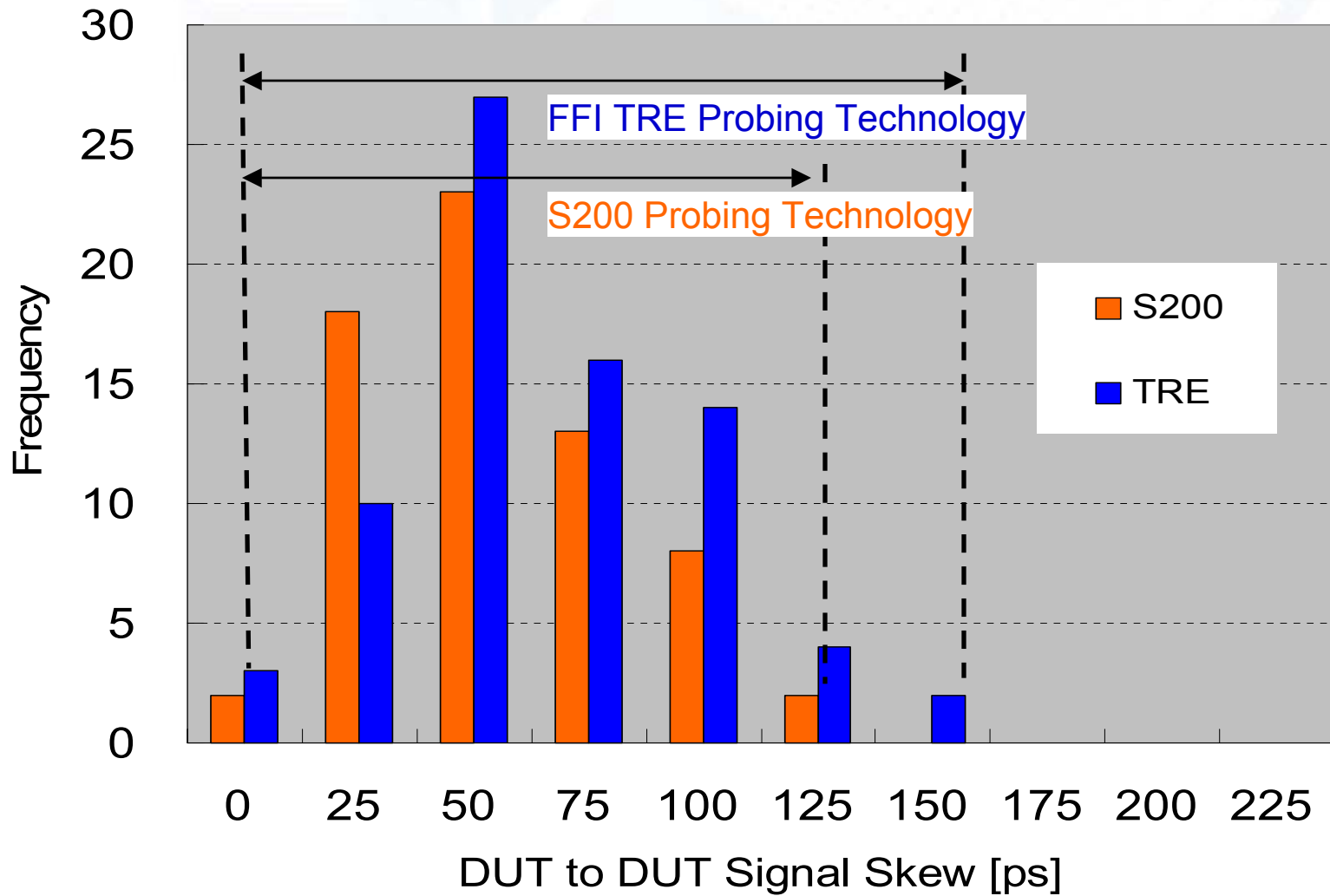
Internal Qualification		S200 Results
Attenuation	-1 dB Bandwidth	225MHz
	-3 dB Bandwidth	850MHz
Rise/Fall Time	20%-80% Tr/Tfl	350 pS
Skew	Channel to Channel	+/- 70 pS
Temperature	Operation Range	-40 to 125°C
Parallelism	Driver Sharing Level	x2
	// per Station	128//

# Wafer-Level Final-Sort Test Customer Qualification

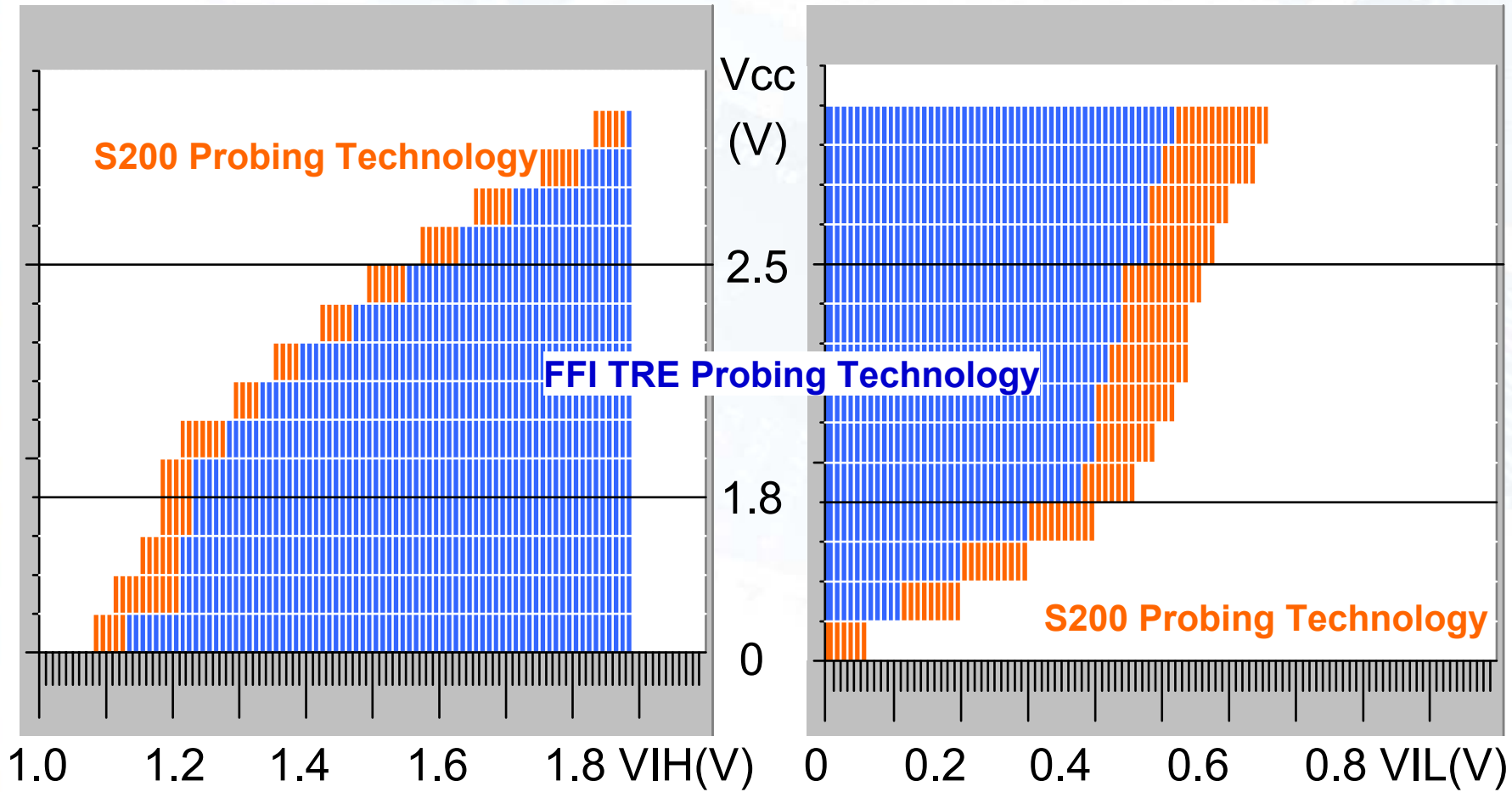
- 143MHz tester + 100MHz Mobile RAM
  - Output pin waveform
  - DQ signal skew
  - Input and output voltage margins
  - Vcc margin
  - Timing margin
  - Wafer-to-wafer high-speed binning correlation



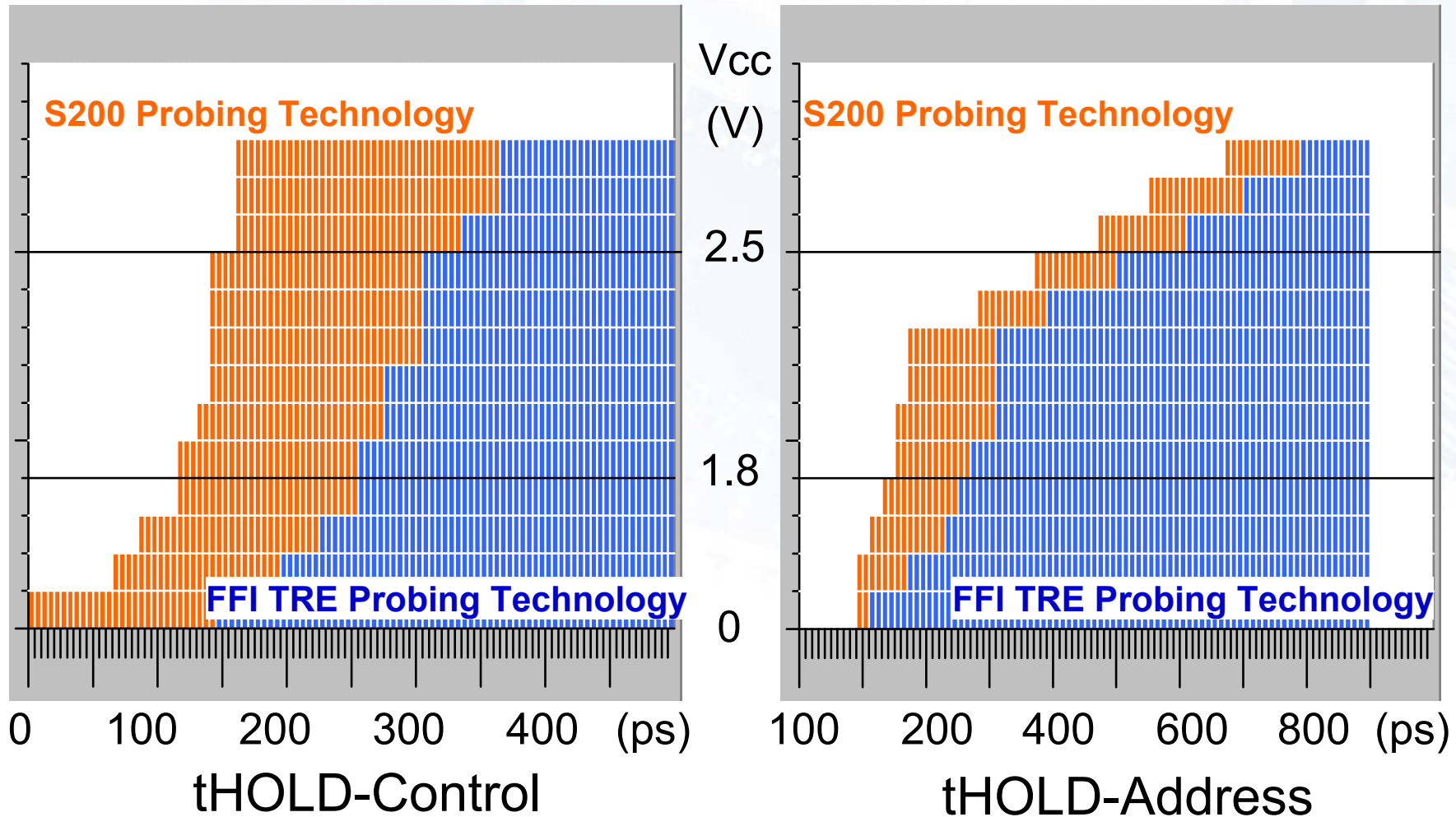
# Customer qualification: DUT to DUT Skew



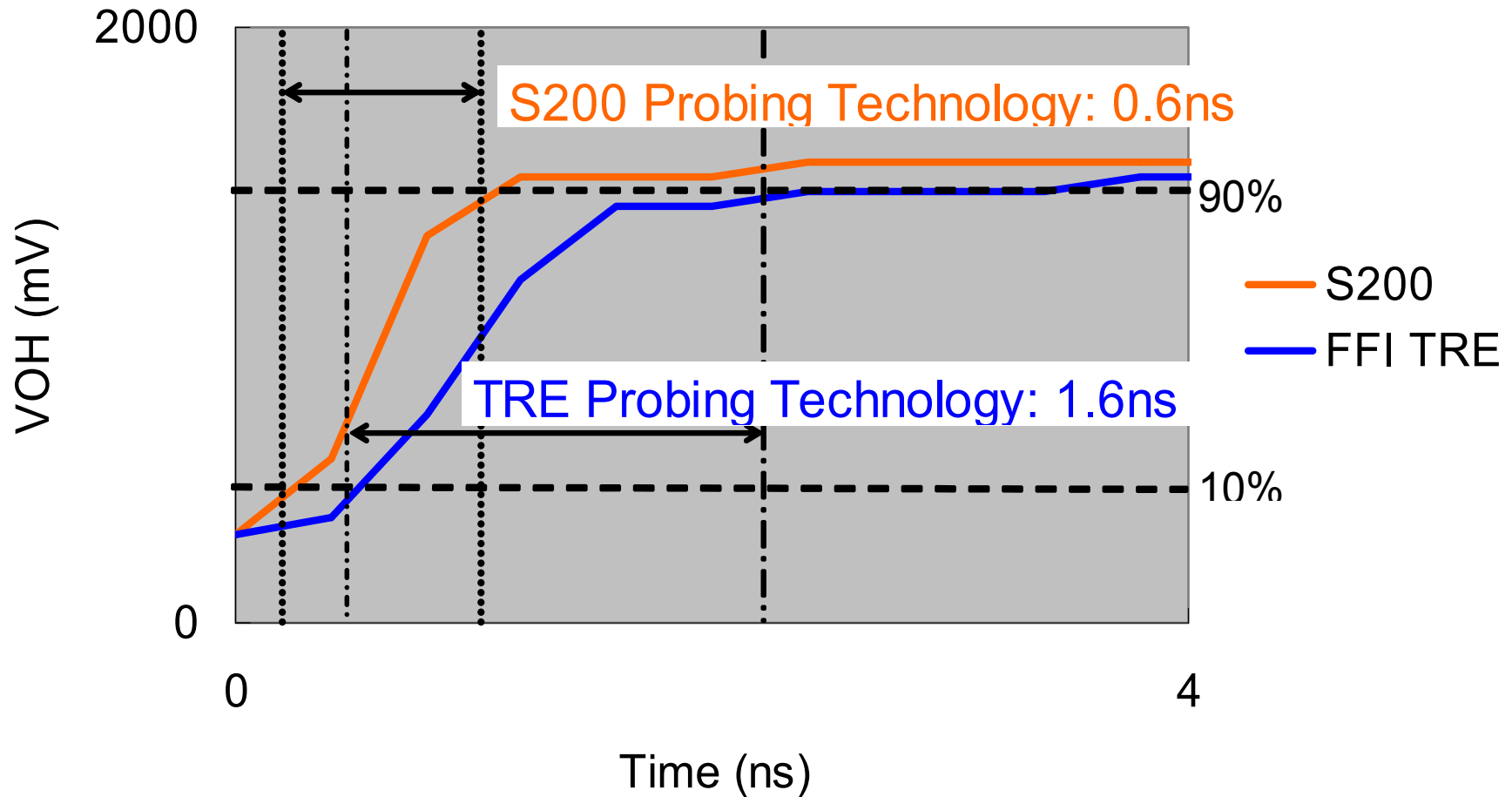
# Customer qualification: VIH/VIL Margin Shmoo



# Customer qualification: tHOLD-Control / tHOLD-Address Margin Shmoo



# Customer Qualification: DQ SMHOO Plot



# Summary and Conclusion

Objectives	Results
High-frequency testing	100MHz beta evaluation
Low TCOO	128 parallel per station
	1.5x throughput compared with non-TRE probing
	1.1x throughput compared with low-frequency testing
Wide temperature	Low-to-high temperature testing throughout the test process
On-spec testing	To be applied to 133MHz Mobile RAM at device speed testing

# Follow-on Work

- Elpida Memory Inc.
  - 100MHz Mobile RAM production using S200
  - Evaluation of 133MHz Mobile RAM at-device-speed testing with S200
- FormFactor, Inc.
  - Customer qualification for 133MHz and beyond
  - Beta site evaluation of multi-bit FLASH memory 100MHz and beyond

# Project Members

- Elpida
  - Masahide Ozawa
  - Yozo Saiki
  - Koji Mine
  - Katsuji Hoshi
  - Yosuke Kawamata
  - Hajime Sasamoto
  - Satoshi Gomi
  - Tomoharu Yamaguchi
- FormFactor
  - Norishige Kawashimo
  - Mark Brandemuhel
  - Chuck Miller
  - Jim Tseng
  - Ken Matsubayashi
  - Nobuhiro Kawamata

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